

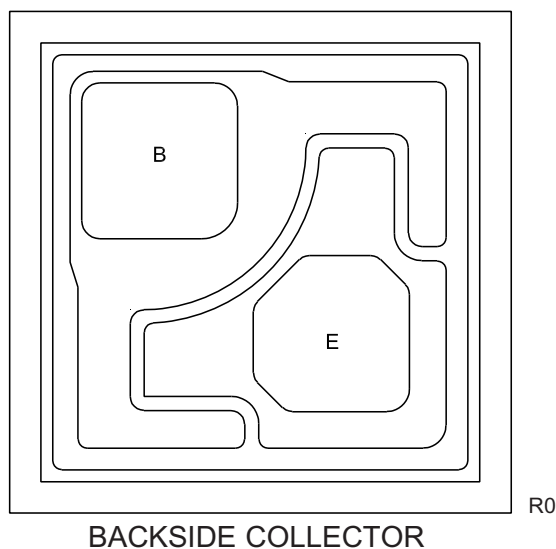
PROCESS CP392V
Smal Signal Transistor
NPN - Amp/Switch Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	11 x 11 MILS
Die Thickness	7.1 MILS
Base Bonding Pad Area	3.7 x 3.7 MILS
Emitter Bonding Pad Area	3.7 x 3.7 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

93,826

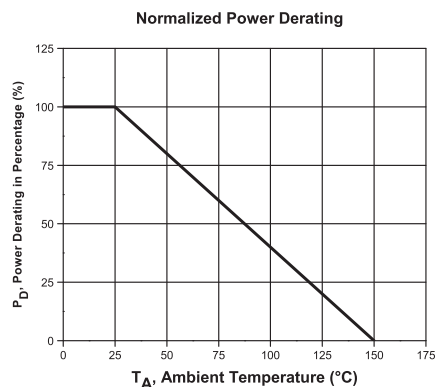
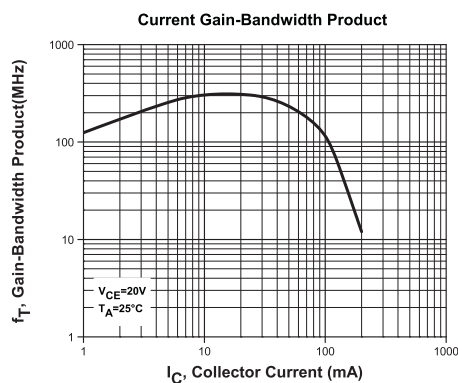
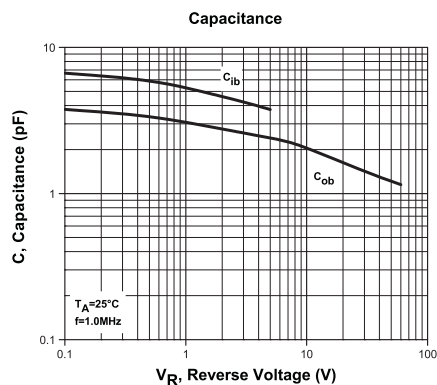
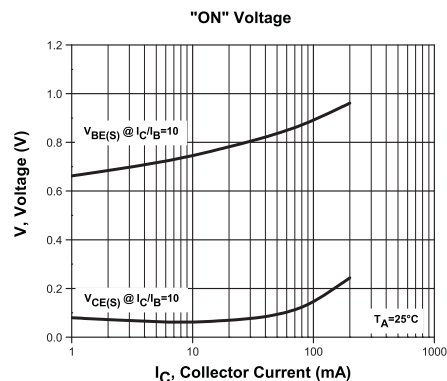
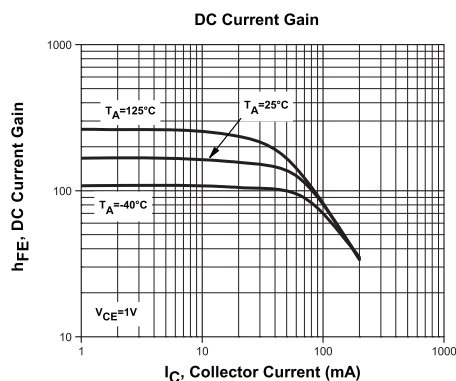
PRINCIPAL DEVICE TYPES

2N3904
CMKT3904
CMLT3904E
CMPT3904
CMPT3904E
CMST3904
CXT3904
CZT3904

R2 (13-May 2010)

PROCESS CP392V

Typical Electrical Characteristics



R2 (13-May 2010)